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Steponas Ašmontas

Jonas Gradauskas

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Introduction

The fifth international conference on Advanced Optical Materials, Technologies, and Devices (AOMD-5) was held 27–30 August 2006 in Vilnius, Lithuania. Vilnius is the historical capital of Lithuania, founded in 1323. The city proudly features the Old Town which is an urban district of tremendous cultural and historic value from a national as well as an international point of view. The biggest Baroque Old Town in the Eastern Europe lies surrounded by green hills. Different cultures have influenced the town in the past, creating an unforgettable fusion that is still present today. The Old Town was inscribed by UNESCO in the World Heritage list in 1994. Day by day, Vilnius is becoming a more modern European city, but still maintains its old world atmosphere.

AOMD-5 belongs to a conference series organized under the auspices of The Baltic Chapter of The International Society for Optical Engineering (SPIE). Continuing the series of forum held in Riga (1996), Vilnius (2000), Riga (2002), and Tartu (2004), the Conference intends to continue the tradition of the exchange of ideas and encourage cooperation between the East and West in the field of optics-related advanced materials and devices. The conference venue was the Conference Hall of Semiconductor Physics Institute. The session topics discussed were

- Optoelectronic Materials and Devices
- Semiconductors and Laser Technology
- Optical and Fiberoptical Devices
- Nanotechnology-Based Multifunctional Materials
- Inorganic and Organic Optical Materials

The 2006 conference had 100 participants from 15 countries. There were 18 invited talks: from P. Andrekson, B. Jaskorzynska (Sweden), A. N. Baranov, S. Barbieri, A. Maestrini (France), A. Freiberg, M. Krunks (Estonia), M. Godlewski, P. Kossacki (Poland), D. Hommel (Germany), M. V. Lebedev, V. Veiko (Russia), I. Muzikante (Latvia), J. S. Penttilä (Finland), S. Juršėnas, J. V. Vaitkus, L. Valkūnas, G. Valušis (Lithuania). There were also 20 contributed papers and 54 poster presentations. Articles related to the conference reports are published in this volume of the Proceedings of SPIE.

Many thanks are rendered to all participants who made the conference significant, to all authors, and to all reviewers of the manuscripts.

**Steponas Ašmontas
Jonas Gradauskas**

